**Product data sheet** 

## 1. General description

Dual Silicon Carbide Schottky diode in a TO247 plastic package, designed for high frequency switching mode power supplies.



AEC - Q101 Qualified

### 2. Features and benefits

- Highly stable switching performance
- High forward surge capability I<sub>FSM</sub>
- · Extremely fast reverse recovery time
- · Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant
- High junction operating temperature capability (T<sub>i(max)</sub> = 175 °C)
- AEC-Q101 qualified

## 3. Applications

- · EV On Board Chargers
- EV DC-DC converters
- Other EV HV systems

### 4. Quick reference data

### Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values		Unit		
Absolute	Absolute maximum rating							
$V_{RRM}$	repetitive peak reverse voltage			1200			V	
Io	limiting average forward current	T <sub>mb</sub> ≤ 134 °C; DC; both diodes			30		А	
T <sub>j</sub>	junction temperature			-55 to 175		°C		
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit	
Static ch	aracteristics							
$V_{F}$	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 5</u>		-	1.42	1.60	V	
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; per diode; <u>Fig. 5</u>		-	1.90	2.30	V	
Dynamic	characteristics						-	
Q <sub>r</sub>	recovered charge	$I_F = 15 \text{ A}$ ; $dI_F/dt = 500 \text{ A/}\mu\text{s}$ ; $V_R = 400 \text{ V}$ ; $T_j = 25 ^{\circ}\text{C}$ ; per diode; Fig. 7		-	36	-	nC	

# 5. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode		
2	K	cathode		A1
3	A2	anode		K
mb	mb	mounting base; connected to cathode		sym125

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package name	Orderable part number		Small packing guantity		Package issue date
	Haine		memou	quantity	Version	issue uate
WNSC2D301200CW-A	TO247	WNSC2D301200CW-A6Q	Tube	30	TO247P	09-Mar-2023

# 7. Marking

### Table 4. Marking codes

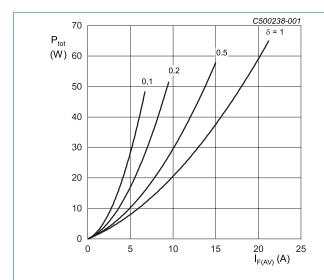
Type number	Marking codes
WNSC2D301200CW-A	WNSC2D 301200CW-A

# 8. Limiting values

### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage			1200	V
$V_{RWM}$	crest working reverse voltage			1200	V
$V_R$	reverse voltage	DC		1200	V
Io	limiting average forward	T <sub>mb</sub> ≤ 134 °C; DC; both diodes		30	Α
	current	T <sub>mb</sub> ≤ 125 °C; DC; both diodes		34	Α
		T <sub>mb</sub> ≤ 25 °C; DC; both diodes		66	Α
I <sub>FRM</sub>	repetitive peak forward current	$δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_{mb} \le 125 °C$ ; square-wave pulse; per diode		26	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode		150	А
		$t_p$ = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse; per diode		1100	Α
l²t	I <sup>2</sup> t for fusing	sine-wave pulse; $T_{j(init)} = 25  ^{\circ}C$ ; $t_p = 10  \text{ms}$		113	A <sup>2</sup> s
T <sub>stg</sub>	storage temperature			-55 to 175	°C
T <sub>j</sub>	junction temperature			-55 to 175	°C



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$  $V_0 = 1.150 \text{ V}; R_s = 0.0901 \Omega$ 

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode

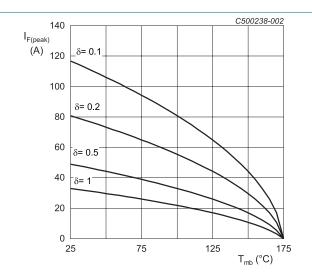
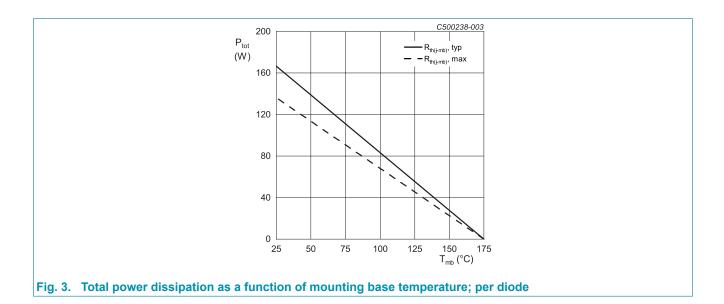


Fig. 2. Current derating as a function of mounting base temperature; per diode



## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance	per diode; Fig. 4		-	0.9	1.1	K/W
	from junction to mounting base	both diodes conducting		-	0.46	0.6	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air		-	40	-	K/W

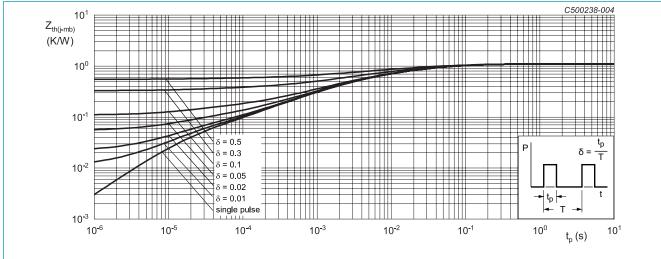
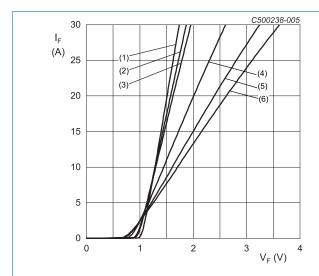


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit	
Static cha	Static characteristics							
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 5</u>		-	1.42	1.60	V	
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; per diode; <u>Fig. 5</u>		-	1.90	2.30	V	
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 175 °C; per diode; <u>Fig. 5</u>		-	2.00	2.50	V	
I <sub>R</sub>	reverse current	V <sub>R</sub> = 1200 V; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 6</u>		-	1	75	μΑ	
		V <sub>R</sub> = 1200 V; T <sub>j</sub> = 175 °C; per diode; <u>Fig. 6</u>		-	25	-	μΑ	
Dynamic	characteristics							
Q <sub>r</sub>	recovered charge	$I_F = 15 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 500 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; per diode; Fig. 7		-	36	-	nC	
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 1 V; T <sub>j</sub> = 25 °C		-	694	-	pF	
		f = 1 MHz; V <sub>R</sub> = 400 V; T <sub>j</sub> = 25 °C		-	64	-	pF	
		f = 1 MHz; V <sub>R</sub> = 800 V; T <sub>j</sub> = 25 °C		-	48	-	pF	
E <sub>as</sub>	non-repetitive avalanche energy	$I_R = 4.7 \text{ A}$ ; L = 10 mH; $T_{j(init)} = 25 ^{\circ}\text{C}$ ; per diode		110	-	-	mJ	



 $V_o = 1.150 \text{ V}; R_s = 0.0901 \Omega$ 

(1) T<sub>i</sub> = -55 °C; typical values

(2) T<sub>i</sub> = 0 °C; typical values

(3) T<sub>j</sub> = 25 °C; typical values (4) T<sub>j</sub> = 100 °C; typical values

(5)  $T_j = 150$  °C; typical values

(6) T<sub>i</sub> = 175 °C; typical values

Fig. 5. Forward current as a function of forward voltage; typical values; per diode

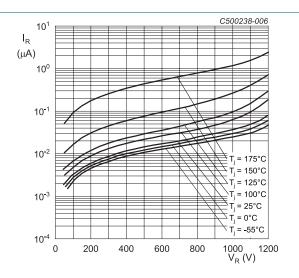


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value; per diode

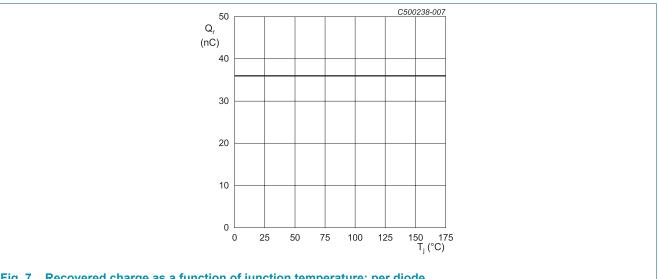
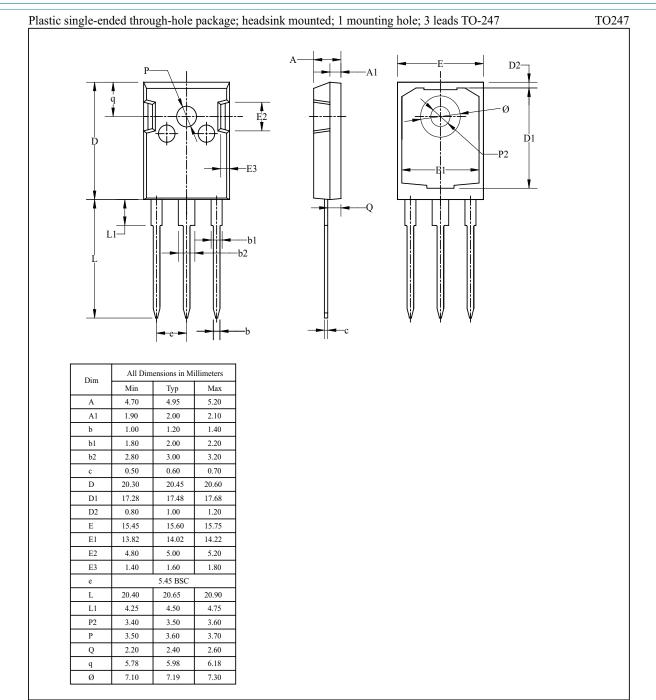


Fig. 7. Recovered charge as a function of junction temperature; per diode

# 11. Package outline



## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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For more information, please visit: http://www.ween-semi.com
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